

General Description

The AGM614MNA combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

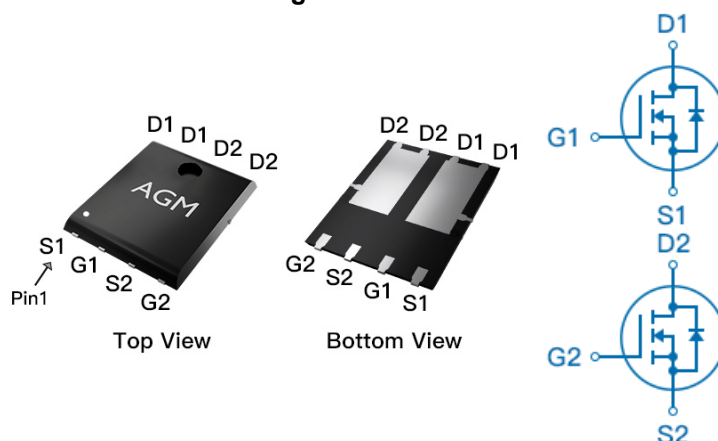
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	13mΩ	40A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM614MNA	AGM614MNA	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage ($V_{GS}=0V$)	60	V
VGS	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
ID	Drain Current-Continuous($T_c=25^{\circ}\text{C}$) (Note 1)	40	A
	Drain Current-Continuous($T_c=100^{\circ}\text{C}$)	24	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	160	A
PD	Maximum Power Dissipation($T_c=25^{\circ}\text{C}$)	20.8	w
	Maximum Power Dissipation($T_c=100^{\circ}\text{C}$)	8.3	w
EAS	Avalanche energy (Note 3)	56	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	--	20	$^{\circ}\text{C}/\text{W}$
RθJC	Thermal Resistance Junction-Case ¹	---	6.0	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.6	2.2	V
gFS	Forward Transconductance	VDS=5V, ID=6A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	13	17	mΩ
		VGS=4.5V, ID=6A	--	20	25	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=30V, VGS=0V, F=1MHZ	--	510	--	pF
Coss	Output Capacitance		--	170	--	pF
Crss	Reverse Transfer Capacitance		--	11	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V, VDS=30V, ID=8A, RGEN=3Ω	--	6.0	--	nS
tr	Turn-on Rise Time		--	4.0	--	nS
td(off)	Turn-Off Delay Time		--	25	--	nS
tf	Turn-Off Fall Time		--	3.0	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=8A	--	11.7	--	nC
Qgs	Gate-Source Charge		--	2.0	--	nC
Qgd	Gate-Drain Charge		--	3.5	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	40	A
VSD	Forward on Voltage	VGS=0V, IS=10A	--	--	1.2	V
trr	Reverse Recovery Time	IF=10A , di/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1. The maximum current rating is package limited.

Notes 2. Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3. EAS condition: T_J=25°C, VDD=30V, Vgs=10V, ID=15A, L=0.5mH, RG=25ohm

Typical Characteristics

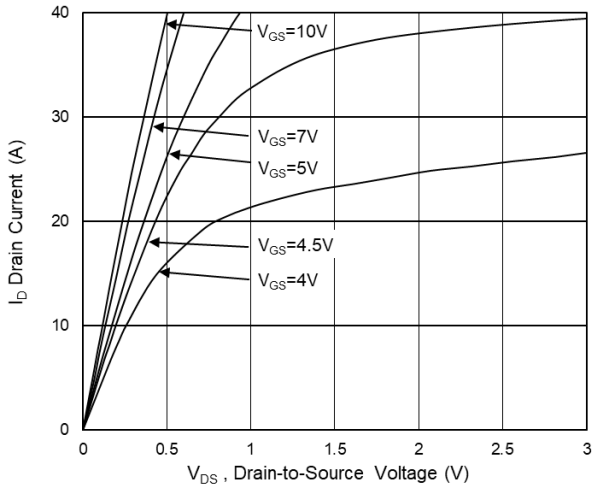


Fig.1 Typical Output Characteristics

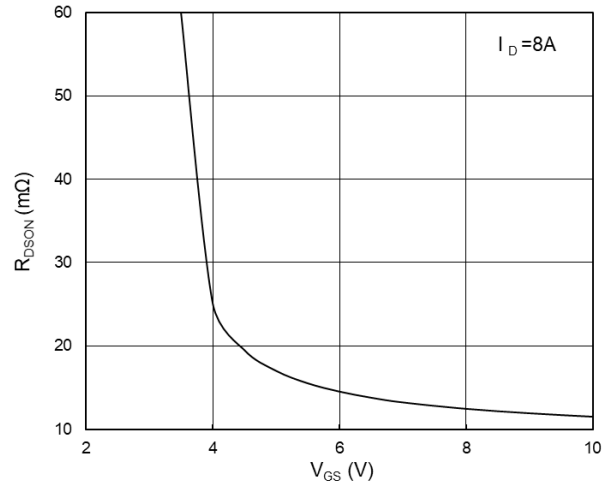


Fig.2 On-Resistance vs G-S Voltage

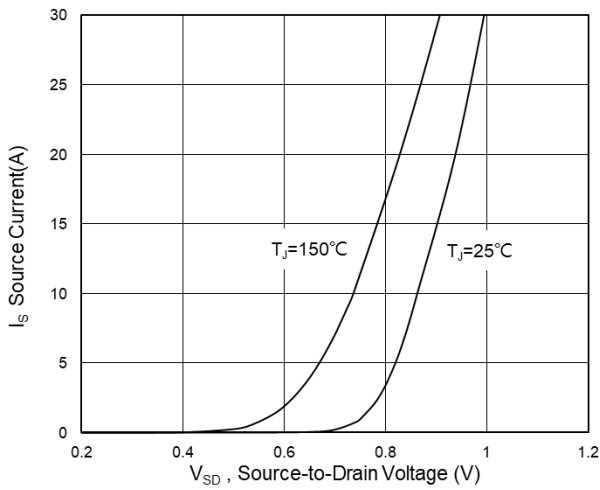


Fig.3 Source Drain Forward Characteristics

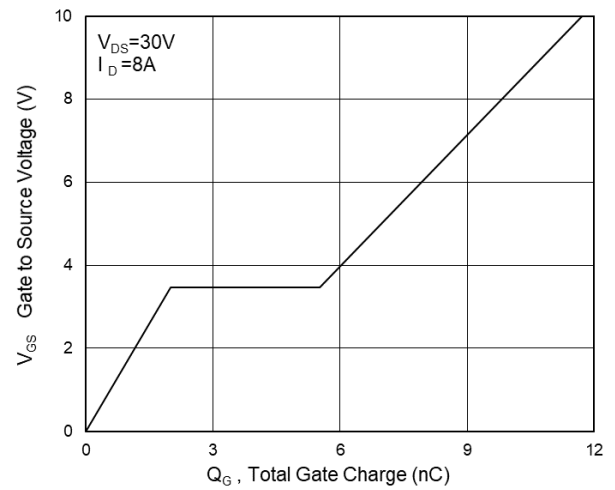


Fig.4 Gate-Charge Characteristics

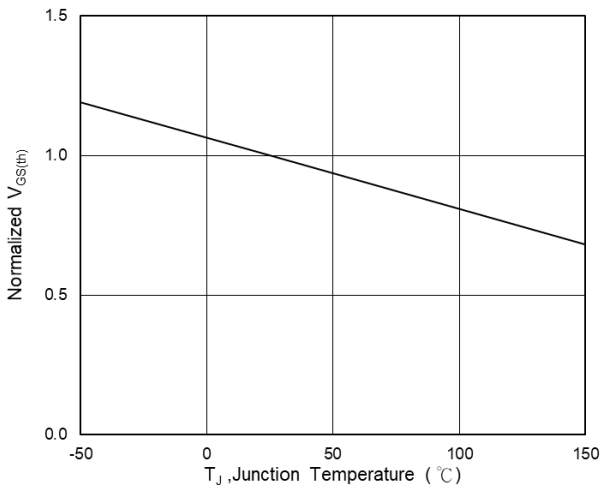


Fig.5 Normalized $V_{GS(th)}$ vs T_J

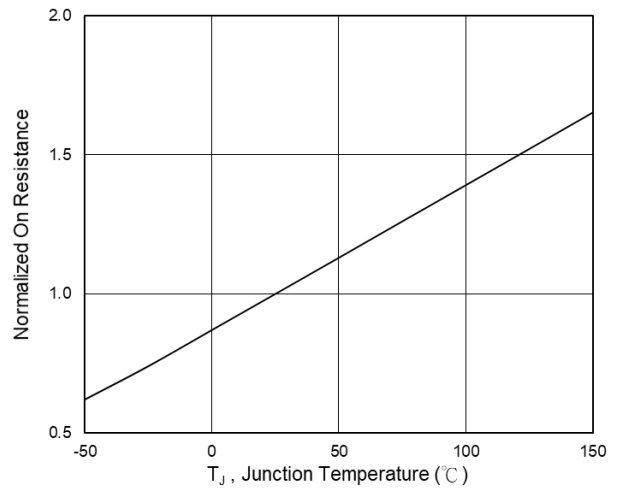


Fig.6 Normalized $R_{DS(ON)}$ vs T_J

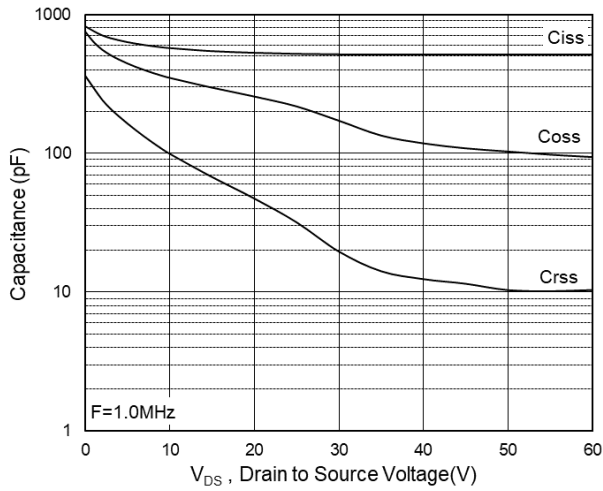


Fig.7 Capacitance

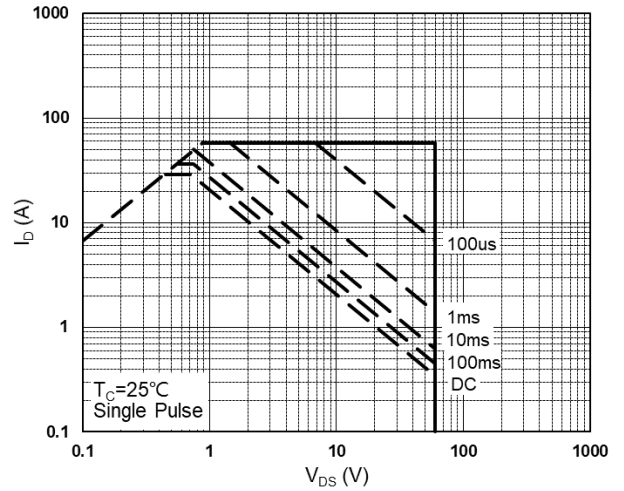


Fig.8 Safe Operating Area

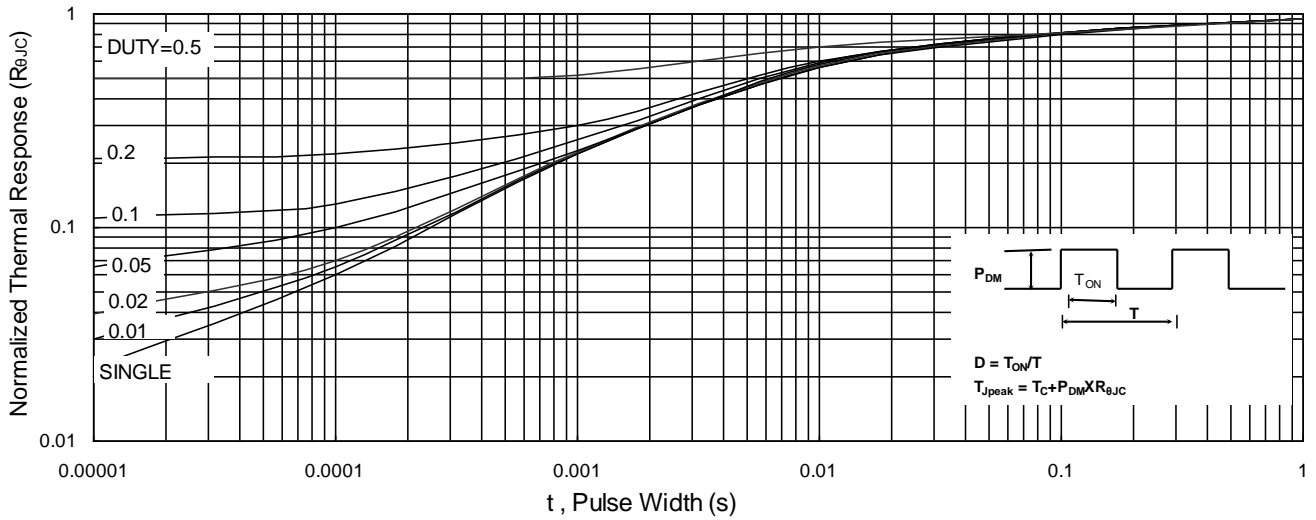


Fig.9 Normalized Maximum Transient Thermal Impedance

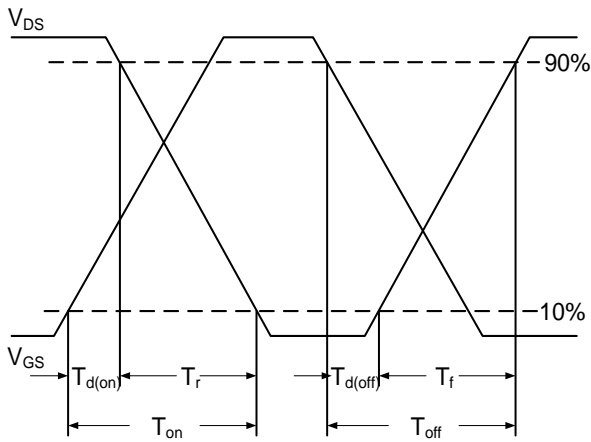


Fig.10 Switching Time Waveform

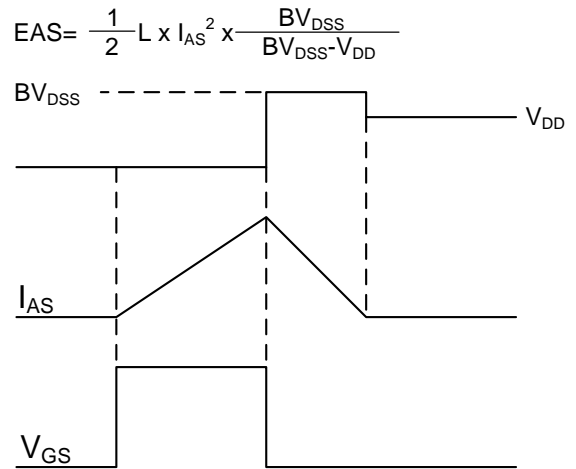
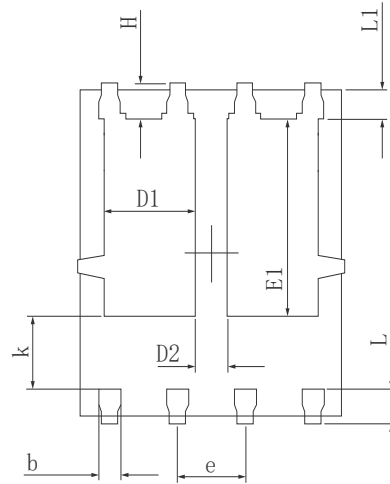
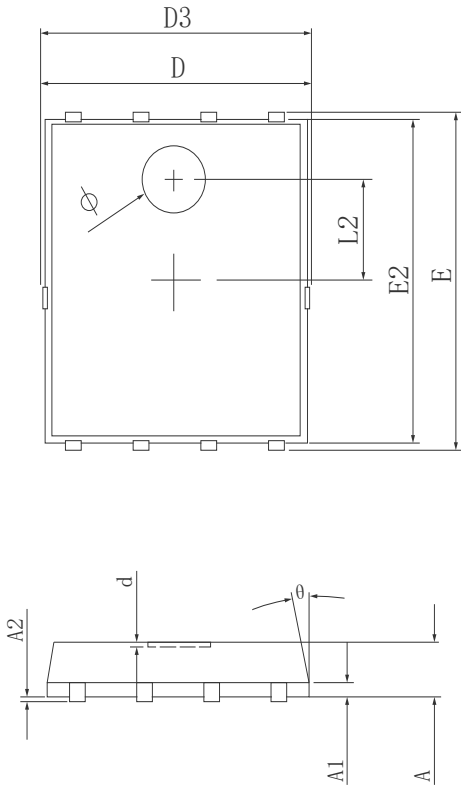
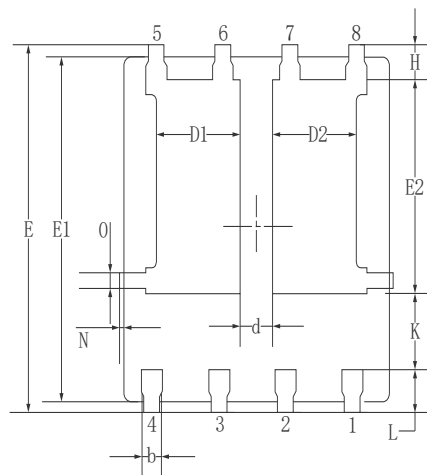
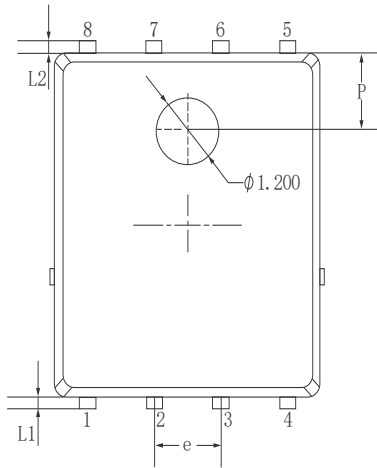


Fig.11 Unclamped Inductive Waveform

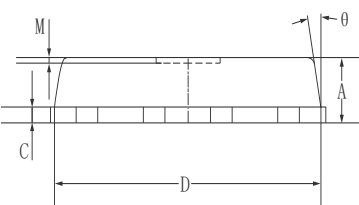
•Dimensions (PDFN5*6)



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	1.605	1.705	1.805
D2	0.500	0.600	0.700
D3	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
theta	8°	10°	12°
phi	1.100	1.200	1.300
d			0.100



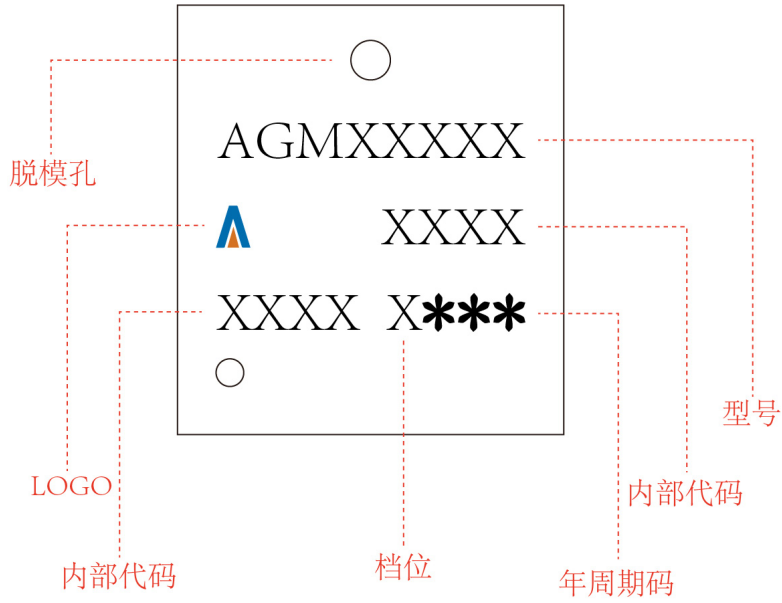
Symbol	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.61	1.71
d	0.50	0.60	0.70
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
theta	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		



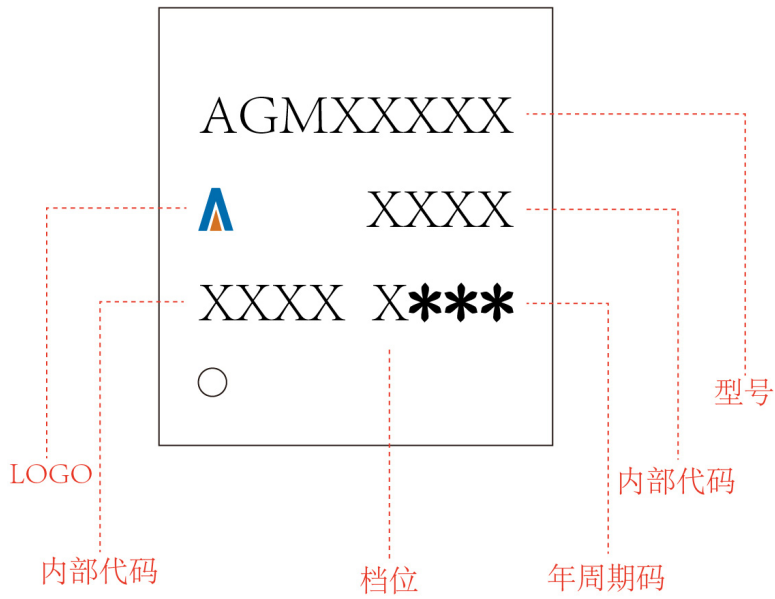
PDFN5*6

Marking Instructions:

Model1:



Model2:




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